Journal of Crystal Growth 107 (1991) 1077–1090
North-Holland

AUTHOR INDEX

Abernathy, C.R., Carbon incorporation in GaAs and AlGaAs grown by MOMBE using trimethylgallium 107 (1991) 982
Abernathy, C.R., see Bohling 107 (1991) 1068
Abraham, P., A. Bekkaoui, V. Soulière, J. Bouix and Y. Monteil, Thermal decomposition studies of group V hydrides 107 (1991) 26
Achargui, N., A. Benachemhou, A. Foucaran, G. Bougnot, P. Coulon, J.P. Laurenti and J. Camassel, Hetero-epitaxy of $ZnSiAs_2$/GaAs grown by atmospheric pressure MOVPE 107 (1991) 410
Ackaert, A., P. Demeester, L. Buydens, G. Coudenys, P. Van Daele and M. Renaud, Selective MOVPE growth of GaAs on Si and its applications to LEDs 107 (1991) 822
Ahlgren, W.L., see Tompa 107 (1991) 198
Ahrenkiel, R.K., see Venkatasubramanian 107 (1991) 489
Aihara, N., see Onuma 107 (1991) 360
Aina, L., M. Mattingly, M. Serio and E. Martin, MOVPE of AlInAs HEMT structures 107 (1991) 932
Akasaki, I., see Hiramatsu 107 (1991) 509
Albrecht, H., see Ebbinghaus 107 (1991) 840
Alexandre, F., see Benchimol 107 (1991) 978
Allen, J.T., see Pemble 107 (1991) 37
Alwan, J.J., see York 107 (1991) 741
Amano, H., see Hiramatsu 107 (1991) 509
Anayama, C., see Kondo 107 (1991) 578
Anderson, P.L., see Tompa 107 (1991) 198
Andersson, J.Y., see Paska 107 (1991) 845
Ando, H., see Fujii 107 (1991) 1030
André, J.P., see Mpaskoutas 107 (1991) 192
André, J.P., J.N. Patillon, P. Riglet, J.Y. Lesiourd, H. Le Coz and B.G. Martin, High optical and electrical quality GaInAs/InP, GaAs/InP double heterostructures for optoelectronic integration 107 (1991) 855
Annapragada, A.V., K.F. Jensen and T.F. Kuech, Infrared spectroscopic determination of substitutional carbon in MOVPE grown films of GaAs 107 (1991) 248
Aoyagi, Y., see Iwai 107 (1991) 136
Araki, S., see Takeda 107 (1991) 351
Asahi, H., T. Kaneko, Y. Okuno and S. Gonda, MOMBE (metalorganic molecular beam epitaxy) growth of InGaAlAsSb system on GaSb 107 (1991) 1009
Asai, K., see Fujita 107 (1991) 473
Asaka, M., see Ashizawa 107 (1991) 903
Ashizawa, Y., T. Noda, K. Morizuka, M. Asaka and M. Obara, LPMOCVD growth of C doped GaAs layers and AlGaAs/GaAs heterojunction bipolar transistors 107 (1991) 903
Asonen, H., see Tapurra 107 (1991) 1070
Aspnes, D.E., see Colas 107 (1991) 47
Aspnes, D.E., see Quinn 107 (1991) 1045
Aulombard, R.L., see Pagès 107 (1991) 670
Autore, G., see Genova 107 (1991) 1065
Azoulay, R., see Draïdia 107 (1991) 483
Azoulay, R., A. Clei, L. Dugrand, N. Draïdia, G. Le Roux and S. Biblemont, Electrical and structural characterization of GaAs on InP grown by OMCVD; application to GaAs MESFETs 107 (1991) 926

Balk, P., see Wisser 107 (1991) 111
Balk, P., see Kayser 107 (1991) 141
Balk, P., see Finders 107 (1991) 151
Balk, P., see Behet 107 (1991) 209
Balk, P., see Pohl 107 (1991) 309
Balk, P., see Zimmer 107 (1991) 348
Balk, P., see Hövel 107 (1991) 355
Balk, P., see Hergeth 107 (1991) 537
Balk, P., see Musolf 107 (1991) 1043
Baur, B., see Heinecke 107 (1991) 1062
Bedair, S.M., see Gong 107 (1991) 83
Bedair, S.M., see McDermott 107 (1991) 96
Bedair, S.M., see Liu 107 (1991) 878
Beernink, K.J., see York 107 (1991) 741
Behet, M., A. Brauers and P. Balk, Plasma MOVPE of ternary and quaternary layers 107 (1991) 209
Bekkaoui, A., see Abraham 107 (1991) 26
Benachemhou, A., see Achargui 107 (1991) 410
Benchimol, J.L., G. Le Roux, H. Thibierge, C. Daguet, F. Alexandre and F. Brillouet, Incorporation of group III and group V elements in chemical beam epitaxy of GaInAsP alloys 107 (1991) 978
Bhat, R., see Colas 107 (1991) 47
Bhat, R., see Caneau 107 (1991) 203
Bhat, R., see Colas 107 (1991) 226
Bhat, R., see Colas 107 (1991) 243
Bhat, R., E. Kapon, S. Simhony, E. Colas, D.M. Hwang, N.G. Stoffel and M.A. Koza, Quantum wire lasers by OMCVD growth on nonplanar substrates 107 (1991) 716

Bhat, R., C. Caneau, C.E. Zah, M.A. Koza, W.A. Bonner, D.M. Hwang, S.A. Schwarz, S.G. Menocal and F.G. Favire, Orientation dependence of S, Zn, Si, Te, and Sn doping in OMCVD growth of InP and GaAs: application to DH lasers and lateral p–n junction arrays grown on non-planar substrates 107 (1991) 772

Bhat, R., M.A. Koza, C.E. Zah, C. Caneau, C.C. Chang, S.A. Schwarz, A.S. Gozdz, P.S.D. Lin and A. Yi-Yan, A novel technique for the preservation of gratings in InP and InGaAsP and for the simultaneous preservation of InP, InGaAs, and InGaAsP in OMCVD 107 (1991) 871

Biblemont, S., see Azoulay 107 (1991) 926

Biefeld, R.M., J.R. Wendt and S.R. Kurtz, Improving the performance of $InAs_{1-x}Sb_x$/InSb infrared detectors grown by metalorganic chemical vapor deposition 107 (1991) 836

Bimberg, D., see Wolf 107 (1991) 381

Bimberg, D., see Grundmann 107 (1991) 494

Bimberg, D., see Böhrer 107 (1991) 555

Boermans, M.J.B., see Valster 107 (1991) 403

Bohling, D.A., G.T. Muhr, C.R. Abernathy, A.S. Jordan, S.J. Pearton and W.S. Hobson, The search for all-hydride MOMBE: examination of trimethylamine alane, trimethylamine gallane, and arsine 107 (1991) 1068

Böhrer, J., M. Grundmann, U. Lienert, D. Bimberg, H. Ishikawa, M. Kamada and N. Watanabe, Determination of the band discontinuity of MOCVD grown $In_{1-x}Ga_xAs/In_{1-y}Al_yAs$ heterostructures with optical and structural methods 107 (1991) 555

Bollig, B., see Lakner 107 (1991) 452

Bona, G.L., see Roentgen 107 (1991) 724

Bonner, W.A., see Bhat 107 (1991) 772

Bottka, N., D.K. Gaskill, P.D. Wright, R.W. Kaliski and D.A. Williams, Qualification of OMVPE AlGaAs/GaAs HBT structures using nondestructive photoreflectance spectroscopy 107 (1991) 893

Bougnot, G., see Achargui 107 (1991) 410

Bougnot, G., F. Delannoy, F. Pascal, P. Grosse, A. Giani, J. Kaoukab, J. Bougnot, R. Fourcade, P.J. Walker, N.J. Mason and H. Lambert, Improvement of the crystalline, optical and electrical quality of MOVPE GaInSb layers 107 (1991) 502

Bougnot, J., see Bougnot 107 (1991) 502

Bouix, J., see Abraham 107 (1991) 26

Bourdillot, M., see Smith 107 (1991) 605

Bove, Ph., see Maurel 107 (1991) 1076

Brauers, A., see Behet 107 (1991) 209

Brauers, A., Alternative precursors for III–V MOVPE criteria for evaluation 107 (1991) 281

Brauers, A., see Pohl 107 (1991) 309

Brauers, A., see Zacheja 107 (1991) 314

Brauers, A., see Zimmer 107 (1991) 348

Brauers, A., see Hövel 107 (1991) 355

Brianese, N., see Hövel 107 (1991) 355

Briggs, A.T.R., see Cureton 107 (1991) 549

Brillouet, F., see Benchimol 107 (1991) 978

Briot, O., see Pagès 107 (1991) 670

Brown, P.D., see Simmons 107 (1991) 664

Brysch, W., see Zimmer 107 (1991) 348

Buchan, N.I., T.F. Kuech, M.A. Tischler and R. Potemski, Epitaxial growth of GaAs with $(C_2H_5)_2GaCl$ and AsH_3 in a hot-wall system 107 (1991) 331

Buhaenko, D.S., see Pemble 107 (1991) 37

Bulle-Lieuwma, C.W.T., see Valster 107 (1991) 403

Burkhard, H., see Haacke 107 (1991) 342

Button, C.C., see Roberts 107 (1991) 915

Buydens, L., see Demeester 107 (1991) 161

Buydens, L., see Ackaert 107 (1991) 822

Byrne, C.F., see Smith 107 (1991) 605

Camassel, J., see Achargui 107 (1991) 410

Camassel, J., J.P. Laurenti, S. Juillaguet, F. Reinhardt, K. Wolter, H. Kurz and D. Grützmacher, Finite interface effects for thin GaInAs/InP quantum wells grown by LP-MOVPE with a growth interruption sequence 107 (1991) 543

Caneau, C., R. Bhat, M. Koza, J.R. Hayes and R. Esagui, Etching of InP by HCl in an OMVPE reactor 107 (1991) 203

Caneau, C., see Colas 107 (1991) 226

Caneau, C., see Bhat 107 (1991) 772

Caneau, C., see Bhat 107 (1991) 871

Cardone, F., see Tischler 107 (1991) 268

Carlin, J.F., A. Rudra, R. Houdré, A. Staehli and M. Ilegems, Growth of GaInAs by chemical beam epitaxy 107 (1991) 1057

Carr, N., see Thompson 107 (1991) 860

Castro-Zavala, J.G., see Peña-Sierra 107 (1991) 337

Chang, C.C., see Bhat 107 (1991) 871

Chen, C.Y., see Colas 107 (1991) 243

Chen, Q., see Dapkus 107 (1991) 73

Chern, C.S., see McKee 107 (1991) 445

Chern, C.S., see Zhao 107 (1991) 699

Cheuvart, P., see Desjonquères 107 (1991) 626

Chiu, T.H., J.E. Cunningham, J.A. Ditzenberger and W.Y. Jan, Growth and diffusion study of carbon doped GaAs superlattice grown by chemical beam epitaxy 107 (1991) 1051

Chung, B.-C., R.T. Green and H.F. MacMillan, High carbon doping of $Al_xGa_{1-x}As$ ($0 \le x \le 1$) by atomic layer epitaxy 107 (1991) 89

Clausen, Jr., E.M., see Colas 107 (1991) 243

Clei, A., see Azoulay 107 (1991) 926

Cockayne, B., see Jones 107 (1991) 297
Cohen, R.M., see Ma 107 (1991) 416
Colas, E., D.E. Aspnes, R. Bhat, S.S. Studna, J.P. Harbison, L.T. Florez, M.A. Koza and V.G. Keramidas, In situ monitoring of crystal growth by reflectance difference spectroscopy 107 (1991) 47
Colas, E., A. Shahar, B.D. Soole, W.J. Tomlinson, J.R. Hayes, C. Caneau and R. Bhat, Lateral and longitudinal patterning of semiconductor structures by crystal growth on nonplanar and dielectric-masked GaAs substrates: application to thickness-modulated waveguide structures 107 (1991) 226
Colas, E., E.M. Clausen, Jr., E. Kapon, D.M. Hwang, S. Simhony, R. Bhat, C.Y. Chen, P.S.D. Lin, L. Schiavone and B. Van der Gaag, Direct evidence of lateral bandgap patterning on stepped structures grown on non-planar, vicinal GaAs surfaces by cathodoluminescence investigations 107 (1991) 243
Colas, E., see Bhat 107 (1991) 716
Cole, S., L. Davis, W.J. Duncan, E.M. Marsh, R.H. Moss, W.J.M. Rothwell, P.S. Skevington and G.D.T. Spiller, Doping level anomalies resulting from exposure to dopant precursors during cooling in MOVPE 107 (1991) 254
Cole-Hamilton, D.J., see McQueen 107 (1991) 325
Coleman, J.J., see York 107 (1991) 741
Colter, P.C., see Gong 107 (1991) 83
Cook, L., see Tompa 107 (1991) 198
Coudenys, G., see Moerman 107 (1991) 175
Coudenys, G., see Ackaert 107 (1991) 822
Coulon, P., see Achargui 107 (1991) 410
Crawley, J., see Moerman 107 (1991) 175
Culshaw, P.N., see McQueen 107 (1991) 325
Cunningham, J.E., see Chiu 107 (1991) 1051
Cureton, C.G., E.J. Thrush and A.T.R. Briggs, Lateral and vertical composition control in MOCVD-grown InP/GaInAs(P) structures 107 (1991) 549
Czuprin, P., see Wisser 107 (1991) 111

Daguet, C., see Benchimol 107 (1991) 978
Dapkus, P.D., B.Y. Maa, Q. Chen, W.G. Jeong and S.P. DenBaars, Atmospheric pressure atomic layer epitaxy: mechanisms and applications 107 (1991) 73
Dapkus, P.D., see Grodzinski 107 (1991) 583
David, J.P.R., see Roberts 107 (1991) 915
Davies, G.J., P.J. Skevington, E.G. Scott, C.L. Franch and J.S. Foord, Some comparisons of chemical beam epitaxy with gas source molecular beam epitaxy 107 (1991) 999
Davis, G.J., see French 107 (1991) 1038
Davis, L., see Cole 107 (1991) 254
De Croon, M.H.J.M., see Giling 107 (1991) 56
Deacon, G.B., see Pain 107 (1991) 632
Decoster, D., see Liu 107 (1991) 878
Delannoy, F., see Bougnot 107 (1991) 502
Demeester, P., L. Buydens, I. Moerman, D. Lootens and P. Van Daele, Non-planar MOVPE growth using a novel shadow-masking technique 107 (1991) 161
Demeester, P., see Moerman 107 (1991) 175
Demeester, P., see Ackaert 107 (1991) 822
DenBaars, S.P., see Dapkus 107 (1991) 73
Deppe, D.G., see Dupuis 107 (1991) 790
Deppert, K., see Samuelson 107 (1991) 68
Deppert, K., see Schmidt 107 (1991) 259
Deppert, K., see Jönsson 107 (1991) 1047
Desjonquères, F., A. Tromson-Carli, P. Cheuvart, R. Druilhe, C. Grattepain, A. Katty, Y. Marfaing, R. Triboulet and D. Lorans, Low temperature growth of (Cd,Hg)Te layers by MOVPE 107 (1991) 626
Dickson, R.S., see Pain 107 (1991) 632
Dip, A., see Gong 107 (1991) 83
Ditzenberger, J.A., see Chiu 107 (1991) 1051
Domen, K., see Kondo 107 (1991) 578
Draïdia, N., R. Azoulay, L. Dugrand, A.C. Papadopoulo, Y. Gao, B. Sermage, P. Ossart and J. Meddeb, Optical quality improvement of MOVPE grown GaAlAs/GaAs double heterostructures on silicon substrates 107 (1991) 483
Draïdia, N., see Azoulay 107 (1991) 926
Druilhe, R., see Desjonquères 107 (1991) 626
Dugrand, L., see Draïdia 107 (1991) 483
Dugrand, L., see Azoulay 107 (1991) 926
Duncan, W.J., see Cole 107 (1991) 254
Duncan, W.M., see Gong 107 (1991) 83
Duncan, W.M., see McDermott 107 (1991) 96
Dupuis, R.D., D.G. Deppe, C.J. Pinzone, N.D. Gerrard, S. Singh, G.J. Zydzik, J.P. van der Ziel and C.A. Green, $In_{0.47}Ga_{0.53}As$–InP heterostructures for vertical cavity surface emitting lasers at 1.65 μm wavelength 107 (1991) 790
Durand, A., see Smith 107 (1991) 605
Durose, K., see Simmons 107 (1991) 664
Dütting, K., see Laube 107 (1991) 156

Ebbinghaus, G., R. Strzoda, T. Scherg, H. Albrecht, R. Penz and C. Lauterbach, Two-step MOVPE growth for planar InP/InGaAs/InP pin–FET combinations with locally diffused buffer layer 107 (1991) 840
Ebert, W., see Rosenzweig 107 (1991) 802
Egawa, T., H. Tada, Y. Kobayashi, T. Soga, T. Jimbo and M. Umeno, Room temperature low threshold CW operation of MOCVD-grown AlGaAs/GaAs SQW

lasers on Si substrates with SiO_2 back-coating 107 (1991) 757
Ekström, O., see Landgren 107 (1991) 573
El-Masry, N.A., see McDermott 107 (1991) 96
El-Masry, N.A., see Karam 107 (1991) 129
Elliman, R., see Pain 107 (1991) 610
Esagui, R., see Caneau 107 (1991) 203
Escobosa, A., see Peña-Sierra 107 (1991) 337
Evans, J.F., see Ho 107 (1991) 376

Fang, Z.M., see Ma 107 (1991) 416
Farari, J., see Liu 107 (1991) 878
Favire, F.G., see Bhat 107 (1991) 772
Feil, W.A., see Wills 107 (1991) 712
Finders, J., J. Geurts, A. Kohl, M. Weyers, B. Opitz, O. Kayser and P. Balk, Composition of selectively grown $In_xGa_{1-x}As$ structures from locally resolved Raman spectroscopy 107 (1991) 151
Finke, M.N., see Valster 107 (1991) 403
Florez, L.T., see Colas 107 (1991) 47
Fontijn, G.M., see Young 107 (1991) 274
Foord, J.S., see Davies 107 (1991) 999
Foord, J.S., see French 107 (1991) 1038
Foord, J.S., A.J. Murrell, D. O'Hare, N.K. Singh, A.T.S. Wee and T.J. Whitaker, Studies of the surface reactivity of novel hydride adduct precursors for CBE growth of III–V compounds 107 (1991) 1040
Fotiadis, D.I., see Jensen 107 (1991) 1
Foucaran, A., see Achargui 107 (1991) 410
Fourcade, R., see Bougnot 107 (1991) 502
Franch, C.L., see Davies 107 (1991) 999
Francis, S.M., see Pemble 107 (1991) 37
Franke, D., see Rosenzweig 107 (1991) 802
French, C.L., A.T.S. Wee, J.S. Foord and G.J. Davies, Mechanistic aspects relating to the growth of $Ga_xIn_{1-x}As$ by CBE 107 (1991) 1038
Frijlink, P.M., J.L. Nicolas and P. Suchet, Layer uniformity in a multiwafer MOVPE reactor for III–V compounds 107 (1991) 166
Fröhlich, K., see Souc 107 (1991) 710
Fujii, S., see Fujita 107 (1991) 621
Fujii, T., H. Ando, A. Sandhu, H. Ishikawa and Y. Sugiyama, Gas-source MBE growth and n-type doping of AlGaAs using TEG, TEA, AsH_3 and Si_2H_6 107 (1991) 1030
Fujimoto, T., see Yoshikawa 107 (1991) 653
Fujita, K., Y. Shiba and K. Asai, MOCVD growth of GaAs on Si using (Al,In)GaAs/GaAs buffer layer 107 (1991) 473
Fujita, Sg., see Fujita 107 (1991) 644
Fujita, Sg., see Fujita 107 (1991) 674
Fujita, Sg., see Kawakami 107 (1991) 1072
Fujita, Sz., S. Maruo, H. Ishio, P.A. Murawala and Sg. Fujita, Surface photochemical reactions for alkyl group elimination from precursors in OMVPE 107 (1991) 644
Fujita, Sz., S. Hayashi, M. Funato, T. Yoshie and Sg. Fujita, Properties of $Zn_{1-x}Cd_xS$ ternary and $Zn_{1-x}Cd_xS_{1-y}Se_y$ quaternary thin films on GaAs grown by OMVPE 107 (1991) 674
Fujita, Sz., see Kawakami 107 (1991) 1072
Fujita, Y., T. Terada, S. Fujii and T. Iuchi, Reaction measurements and growth of HgTe/CdTe by photo-assisted MOCVD using an excimer laser 107 (1991) 621
Fukui, T. and H. Saito, Step-flow growth and fractional-layer superlattices on $(\bar{1}\bar{1}\bar{1})$B GaAs vicinal surfaces 107 (1991) 231
Funato, M., see Fujita 107 (1991) 674
Furuhata, N., H. Shimawaki and A. Okamoto, Selective growth of p^+-GaAs by metal-organic molecular beam epitaxy 107 (1991) 1049

Galeuchet, Y.D. and P. Roentgen, Selective area MOVPE of GaInAs/InP heterostructures on masked and nonplanar (100) and {111} substrates 107 (1991) 147
Gallois, B., see Zhao 107 (1991) 699
Ganière, J.-D., see Ougazzaden 107 (1991) 761
Gao, D., see Pain 107 (1991) 610
Gao Hongkai, Yun Feng, Zhang Jikang, Hou Xun and Gong Ping, Investigation of MOCVD growth of $Al_xGa_{1-x}As$/GaAs and $Al_xGa_{1-x}As$/GaAs/$Al_xGa_{1-x}As$/GaAs multilayer structures with high Al content 107 (1991) 428
Gao, Y., see Draïdia 107 (1991) 483
Gao, Y., see Ougazzaden 107 (1991) 761
Garcia, J.C., see Maurel 107 (1991) 1076
Garrett, B., see Glew 107 (1991) 784
Gaskill, D.K., see Bottka 107 (1991) 893
Gastaldi, L., see Genova 107 (1991) 1065
Genova, F., G. Morello, G. Autore and L. Gastaldi, CBE growth of InGaAs for optoelectronic applications 107 (1991) 1065
Gerling, M., see Pistol 107 (1991) 458
Gerling, M., see Titze 107 (1991) 513
Gerrard, N.D., see Dupuis 107 (1991) 790
Geurts, J., see Finders 107 (1991) 151
Giani, A., see Bougnot 107 (1991) 502
Giapis, K.P., see Patnaik 107 (1991) 390
Giling, L.J. and M.H.J.M. de Croon, Surface processes during growth of GaAs by MOCVD 107 (1991) 56
Giling, L.J., see Tang 107 (1991) 263
Giling, L.J., see Te Nijenhuis 107 (1991) 496
Gladfelter, W.L., see Ho 107 (1991) 376
Glanvill, S.R., see Pain 107 (1991) 632
Glew, R.W., P.D. Greene, G.D. Henshall, C. Lowney, J.P. Stagg, J.E.A. Whiteaway, B.

Garrett and A.G. Norman, Growth and assessment of InGaAs/InGaAlAs/InP multiple quantum well lasers 107 (1991) 784
Gonda, S., see Asahi 107 (1991) 1009
Gong, J.R., P.C. Colter, D. Jung, S.A. Hussien, C.A. Parker, A. Dip, F. Hyuga, W.M. Duncan and S.M. Bedair, Atomic layer epitaxy of $Al_xGa_{1-x}As$ and device quality GaAs 107 (1991) 83
Gong Ping, see Gao 107 (1991) 428
Goorsky, M.S., see Kuech 107 (1991) 116
Goorsky, M.S., see Tischler 107 (1991) 268
Gotoh, H., see Shimoyama 107 (1991) 767
Goulding, P.A., see Pemble 107 (1991) 37
Gozdz, A.S., see Bhat 107 (1991) 871
Grattepain, C., see Desjonquères 107 (1991) 626
Green, C.A., see Dupuis 107 (1991) 790
Green, R.T., see Chung 107 (1991) 89
Greene, P.D., see Glew 107 (1991) 784
Gregory, S., see Quinn 107 (1991) 1045
Grodzinski, P., Y. Zou, J.S. Osinski and P.D. Dapkus, Investiation of $In_xGa_{1-x}As$/GaAs strained quantum well structures grown on non-planar substrates by MOCVD 107 (1991) 583
Grosse, P., see Bougnot 107 (1991) 502
Grote, N., see Rosenzweig 107 (1991) 802
Grundmann, D., see Wisser 107 (1991) 111
Grundmann, M., A. Krost and D. Bimberg, LP-MOVPE growth of antiphase domain free InP on (001) Si using low temperature processing 107 (1991) 494
Grundmann, M., see Böhrer 107 (1991) 555
Grützmacher, D., Growth and analysis of quantum well structures 107 (1991) 520
Grützmacher, D., see Schwedler 107 (1991) 531
Grützmacher, D., see Hergeth 107 (1991) 537
Grützmacher, D., see Camassel 107 (1991) 543
Guimarães, F.E.G., I. Gyuro, F. Scheffer, M. Heuken and K. Heime, Optical and electrical properties of the $Al_xGa_{1-x}As$/GaAs single heterojunctions grown by low pressure MOVPE 107 (1991) 434
Guimarães, F.E.G., see Lakner 107 (1991) 452
Gustafsson, A., see Pistol 107 (1991) 458
Gyuro, I., see Guimarães 107 (1991) 434
Gyuro, I., F. Scheffer, M. Joseph, B. Roth, M. Heuken and K. Heime, Ultralow doping profiles for applications in 3D integrated varactor tuned oscillators grown by MOVPE 107 (1991) 956

Haacke, G., S.P. Watkins and H. Burkhard, Control of residual impurity incorporation in tertiarybutylarsine-grown GaAs 107 (1991) 342
Haegel, N., see Karam 107 (1991) 129
Haga, T., see Hiruma 107 (1991) 440
Hageman, P.R., see Te Nijenhuis 107 (1991) 496
Hails, J.E. and S.J.C. Irvine, Screening of organotellurium compounds for use as MOVPE precursors 107 (1991) 319
Hamaoka, K., see Suemune 107 (1991) 1041
Hanke, C., see Korte 107 (1991) 779
Hanna, M.C., Z.H. Lu, E.W. Mao, T. McCormick, E.G. Oh, A. Majerfeld and D.M. Szmyd, Carbon doping exceeding 10^{20} cm^{-3} in GaAs grown by AP-MOVPE 107 (1991) 279
Harbison, J.P., see Colas 107 (1991) 47
Harde, P., see Wolf 107 (1991) 381
Harde, P., see Reier 107 (1991) 867
Hartmann, U., see Pohl 107 (1991) 309
Hase, I., see Taira 107 (1991) 952
Haven, V., see Karam 107 (1991) 129
Haven, V., see Karam 107 (1991) 591
Hayafuji, N., see Nishimura 107 (1991) 468
Hayashi, H., see Kamei 107 (1991) 567
Hayashi, S., see Fujita 107 (1991) 674
Hayes, J.R., see Caneau 107 (1991) 203
Hayes, J.R., see Colas 107 (1991) 226
Haywood, S.K., R.W. Martin, N.J. Mason, R.J. Nicholas and P.J. Walker, GaSb/InAs heterojunctions grown by MOVPE 107 (1991) 422
Heime, K., see Guimarães 107 (1991) 434
Heime, K., see Lakner 107 (1991) 452
Heime, K., see Gyuro 107 (1991) 956
Heinecke, H., B. Baur, F. Höger, A. Miklis and B. Jobst, On the growth of GaInAs by MOMBE (CBE) 107 (1991) 1062
Henshall, G.D., see Glew 107 (1991) 784
Hergeth, J., D. Grützmacher, F. Reinhardt and P. Balk, Effect of growth parameters on the interfacial structure of GaInAs/InP quantum wells 107 (1991) 537
Heuberger, W., see Roentgen 107 (1991) 724
Heuken, M., see Guimarães 107 (1991) 434
Heuken, M., see Lakner 107 (1991) 452
Heuken, M., see Gyuro 107 (1991) 956
Heyen, M., see Schmitz 107 (1991) 188
Hirai, T. and H. Yamane, MOCVD superconducting oxide films 107 (1991) 683
Hiramatsu, K., H. Amano, I. Akasaki, H. Kato, N. Koide and K. Manabe, MOVPE growth of GaN on a misoriented sapphire substrate 107 (1991) 509
Hirose, F., see Suemitsu 107 (1991) 1015
Hirotani, M., see Kato 107 (1991) 832
Hirtz, J.P., see Maurel 107 (1991) 1076
Hiruma, K., T. Haga, T. Usagawa and A. Ihara, Low contact-resistance GaAs/AlGaAs regrowth interfaces and compositional grading layer formation during growth by metalorganic vapor phase epitaxy 107 (1991) 440

Ho, K.-L., K.F. Jensen, J.-W. Hwang, W.L. Gladfelter and J.F. Evans, MOVPE of AlN and GaN by using novel precursors 107 (1991) 376
Hobson, W.S., see Bohling 107 (1991) 1068
Hockly, M., see Spurdens 107 (1991) 215
Höger, F., see Heinecke 107 (1991) 1062
Honda, Y., see Suemune 107 (1991) 1041
Horikoshi, Y., see Kobayashi 107 (1991) 62
Hornung, V., see Rose 107 (1991) 850
Hostalek, M., see Pohl 107 (1991) 309
Hostalek, M., see Hövel 107 (1991) 355
Hostalek, M., see Scholz 107 (1991) 365
Hou Xun, see Gao 107 (1991) 428
Houdré, R., see Carlin 107 (1991) 1057
Hövel, R., see Pohl 107 (1991) 309
Hövel, R., see Zimmer 107 (1991) 348
Hövel, R., N. Brianese, A. Brauers, P. Balk, M. Zimmer, M. Hostalek and L. Pohl, Growth of InP with novel In and P precursors 107 (1991) 355
Hrib, S., see Souc 107 (1991) 710
Hussien, S.A., see Gong 107 (1991) 83
Hwang, D.M., see Colas 107 (1991) 243
Hwang, D.M., see Bhat 107 (1991) 716
Hwang, D.M., see Bhat 107 (1991) 772
Hwang, J.-W., see Ho 107 (1991) 376
Hyuga, F., see Gong 107 (1991) 83
Hyuga, F., see McDermott 107 (1991) 96

Iga, K., see Uchida 107 (1991) 1055
Ihara, A., see Hiruma 107 (1991) 440
Ikeda, H., see Kawanishi 107 (1991) 1060
Ilegems, M., see Carlin 107 (1991) 1057
Inoue, Y., see Shimoyama 107 (1991) 767
Irikawa, M., see Tanaka 107 (1991) 898
Irvine, S.J.C., see Hails 107 (1991) 319
Ishikawa, H., see Böhrer 107 (1991) 555
Ishikawa, H., see Fujii 107 (1991) 1030
Ishimura, E., see Kimura 107 (1991) 827
Ishio, H., see Fujita 107 (1991) 644
Ismail, K., see Karam 107 (1991) 591
Iuchi, T., see Fujita 107 (1991) 621
Ivan, J., see Souc 107 (1991) 710
Iwai, S., T. Meguro, Y. Aoyagi and T. Miyoshi, Patterned crystal growth of GaAs using laser scanning with atomic layer epitaxy 107 (1991) 136

Jan, W.Y., see Chiu 107 (1991) 1051
Jasinski, T.J., see McKee 107 (1991) 445
Jenkin, G.T., see Smith 107 (1991) 605
Jensen, K.F., D.I. Fotiadis and T.J. Mountziaris, Detailed models of the MOVPE process 107 (1991) 1
Jensen, K.F., see Annapragada 107 (1991) 248
Jensen, K.F., see Ho 107 (1991) 376
Jensen, K.F., see Patnaik 107 (1991) 390
Jeong, W.G., see Daplus 107 (1991) 73
Jeppesen, S., see Samuelson 107 (1991) 68
Jeppesen, S., see Jönsson 107 (1991) 1047
Jiang, B.L., see McDermott 107 (1991) 96
Jimbo, T., see Soga 107 (1991) 479
Jimbo, T., see Egawa 107 (1991) 757
Jobst, B., see Heinecke 107 (1991) 1062
Johnson, E.S., Strong enhancement of band edge PL intensity and improved morphology for AlGaAs grown on lenticular GaAs substrates by low pressure MOVPE 107 (1991) 237
Johnson, S.M., see Tompa 107 (1991) 198
Jones, A.C., P.J. Wright and B. Cockayne, Precursors for II–VI semiconductors: requirements and developments 107 (1991) 297
Jones, A.C. and S.A. Rushworth, Growth of low carbon content $Al_xGa_{1-x}As$ by reduced pressure MOVPE using trimethylamine alane 107 (1991) 350
Jönsson, J., see Samuelson 107 (1991) 68
Jönsson, J., K. Deppert, S. Jeppesen, G. Paulsson, L. Samuelson and P. Schmidt, In situ control of the growing surface in high vacuum MOVPE of GaAs 107 (1991) 1047
Jordan, A.S., see Bohling 107 (1991) 1068
Joseph, M., see Gyuro 107 (1991) 956
Juillaguet, S., see Camassel 107 (1991) 543
Jung, D., see Gong 107 (1991) 83
Jürgensen, H., see Schmitz 107 (1991) 188

Kadoiwa, K., see Nishimura 107 (1991) 468
Kaiser, H., see Reier 107 (1991) 867
Kaliski, R.W., see Bottka 107 (1991) 893
Kamada, M., see Böhrer 107 (1991) 555
Kamei, H. and H. Hayashi, OMVPE growth of GaInAs/InP and GaInAs/GaInAsP quantum wells 107 (1991) 567
Kamp, M., G. Mörsch, M. Weyers and H. Lüth, Correlation of carbon incorporation from TEG and effective V/III 107 (1991) 1053
Kaneko, T., see Asahi 107 (1991) 1009
Kang, S.S., see McKee 107 (1991) 445
Kaoukab, J., see Bougnot 107 (1991) 502
Kapon, E., see Colas 107 (1991) 243
Kapon, E., see Bhat 107 (1991) 716
Karam, N.H., V. Haven, S.M. Vernon, N. El-Masry, E.H. Lingunis and N. Haegel, Selective area epitaxy of GaAs on Si using atomic layer epitaxy by LP-MOVPE 107 (1991) 129
Karam, N.H., A. Mastrovito, V. Haven, K. Ismail, S. Pennycook and H.I. Smith, Patterning and overgrowth of nanostructure quantum well wire arrays by LP-MOVPE 107 (1991) 591
Kasahara, A., see Onuma 107 (1991) 360
Kato, H., see Hiramatsu 107 (1991) 509

Kato, K., see Onuma 107 (1991) 360

Kato, T., H. Susawa, M. Hirotani, T. Saka, Y. Ohashi, E. Shichi and S. Shibata, GaAs/GaAlAs surface emitting IR LED with Bragg reflector grown by MOCVD 107 (1991) 832

Katoh, M., see Shimoyama 107 (1991) 767

Katty, A., see Desjonquères 107 (1991) 626

Kawai, H., see Taira 107 (1991) 952

Kawakami, Y., T. Toyoda, Y.-H. Wu, Sz. Fujita and Sg. Fujita, Effects of surface pre-treatment and hydrogen on ALE of ZnSe on GaAs in MOMBE 107 (1991) 1072

Kawanishi, H. and H. Ikeda, Monolayer epitaxial growth of GaInAs ternary by MOMBE 107 (1991) 1060

Kayser, O., B. Opitz, B. Westphalen, U. Niggebrügge, K. Schneider and P. Balk, Selective embedded growth of GaInAs by low pressure MOVPE 107 (1991) 141

Kayser, O., see Finders 107 (1991) 151

Kayser, O., Selective growth of InP/GaInAs in LP-MOVPE and MOMBE/CBE 107 (1991) 989

Kazmierski, C., see Ougazzaden 107 (1991) 761

Kear, B., see Zhao 107 (1991) 699

Kearley, M.Q., see Thompson 107 (1991) 860

Keramidas, V.G., see Colas 107 (1991) 47

Keyes, B.M., see Venkatasubramanian 107 (1991) 489

Kikkawa, T., H. Tanaka and J. Komeno, MOVPE growth of uniform AlGaAs and InGaAs using organoarsine with inverted-horizontal atmospheric-pressure reactor 107 (1991) 370

Kikuta, T., see Tanaka 107 (1991) 898

Kim, J., see York 107 (1991) 741

Kimura, Tadashi, see Kimura 107 (1991) 827

Kimura, Tatsuya, Tadashi Kimura, E. Ishimura, F. Uesugi, M. Tsugami, K. Mizuguchi and T. Murotani, Improvement of InP crystal quality grown on GaAs substrates and device applications 107 (1991) 827

Kishimoto, A., see Suemune 107 (1991) 1041

Klenk, M., see Wiedemann 107 (1991) 561

Klingert, J.K., see Lum 107 (1991) 290

Knight, D.G., C.J. Miner and B. Watt, Effect of wafer cleavage on composition of In GaAsP grown on InP by low pressure MOCVD 107 (1991) 221

Kobayashi, N., T. Makimoto, Y. Yamauchi and Y. Horikoshi, In-situ monitoring of GaAs growth process in MOVPE by surface photo-absorption method 107 (1991) 62

Kobayashi, Y., see Egawa 107 (1991) 757

Kodama, K., see Ozeki 107 (1991) 102

Koerner, U., see Wiedemann 107 (1991) 561

Kohl, A., see Finders 107 (1991) 151

Kohl, A., see Musolf 107 (1991) 1043

Kohl, D., see Zacheja 107 (1991) 314

Kohl, D., see Schütze 107 (1991) 1036

Koide, N., see Hiramatsu 107 (1991) 509

Komeno, J., see Kikkawa 107 (1991) 370

Komeno, J., see Takikawa 107 (1991) 942

Kondo, M., K. Domen, C. Anayama, T. Tanahashi and K. Nakajima, MOVPE growth and optical properties of Al GaInP/GaInP strained single quantum well structures 107 (1991) 578

Körber, W., see Wiedemann 107 (1991) 561

Kordos, P., see Souc 107 (1991) 710

Korte, L., R. Treichler, M. Schreiber, Ch. Tanner, G. Kristen, C. Hanke and G. Weimann, Interaction of the dopants Mg and Si in $Al_xGa_{1-x}As$/GaAs heterolayers (MOVPE): application to DQW laser structures 107 (1991) 779

Kostial, H., see Schmidt 107 (1991) 259

Koui, T., see Suemune 107 (1991) 1041

Koyama, F., see Uchida 107 (1991) 1055

Koza, M.A., see Colas 107 (1991) 47

Koza, M.A., see Caneau 107 (1991) 203

Koza, M.A., see Bhat 107 (1991) 716

Koza, M.A., see Bhat 107 (1991) 772

Koza, M.A., see Bhat 107 (1991) 871

Knowles, P., see Smith 107 (1991) 605

Kristen, G, see Korte 107 (1991) 779

Krost, A., see Wolf 107 (1991) 381

Krost, A., see Grundmann 107 (1991) 494

Kubalek, E., see Lakner 107 (1991) 452

Kuech, T.F., M.S. Goorsky, M.A. Tischler, A. Palevski, P. Solomon, R. Potemski, C.S. Tsai, J.A. Lebens and K.J. Vahala, Selective epitaxy of GaAs, $Al_xGa_{1-x}As$, and $In_xGa_{1-x}As$ 107 (1991) 116

Kuech, T.F., see Annapragada 107 (1991) 248

Kuech, T.F., see Tischler 107 (1991) 268

Kuech, T.F., see Buchan 107 (1991) 331

Kukimoto, H., MOVPE growth of wide bandgap II–VI materials 107 (1991) 637

Kumabe, H., see Nishimura 107 (1991) 468

Kuroda, Y., see Suemune 107 (1991) 679

Kurpas, P., see Richter 107 (1991) 13

Kurtz, S.R., see Biefeld 107 (1991) 836

Kurz, H., see Camassel 107 (1991) 543

Lakner, H., B. Bollig, E. Kubalek, M. Heuken, K. Heime, F. Scheffer and F.E.G. Guimarães, Scanning transmission electron microscopy of heterointerfaces grown by metalorganic vapor phase epitaxy (MOVPE) 107 (1991) 452

Lakrimi, M., N.J. Mason, R.J. Nicholas, G.B. Stringfellow, G. Summers and P.J. Walker, Absorption characteristics of GaSb/InAs and InSb/InAs SLSs grown on (111) GaAs by MOVPE 107 (1991) 518

Lambert, H., see Bougnot 107 (1991) 502
Landgren, G., P. Ojala and O. Ekström, Influence of the gas switching sequence on the optical properties of ultrathin In GaAs/InP quantum wells 107 (1991) 573
Landgren, G., see Nordell 107 (1991) 909
Lane, P.A., see Martin 107 (1991) 969
Larsen, C.A., see Li 107 (1991) 32
Laube, G., A. Nowitzki, K. Dütting and P. Speier, Selective MOVPE of semi-insulating InP layers for high speed OEICs 107 (1991) 156
Laurenti, J.P., see Achargui 107 (1991) 410
Laurenti, J.P., see Camassel 107 (1991) 543
Lauterbach, C., see Ebbinghaus 107 (1991) 840
Le Coz, H., see André 107 (1991) 855
Le Roux, G., see Azoulay 107 (1991) 926
Le Roux, G., see Benchimol 107 (1991) 978
Lebens, J.A., see Kuech 107 (1991) 116
Lee, G.Y., see Thompson 107 (1991) 921
Lesiourd, J.Y., see André 107 (1991) 855
Levy, H.M., see Thompson 107 (1991) 921
Li, S.H., C.A. Larsen and G.B. Stringfellow, Comparative pyrolysis studies of ethylarsines 107 (1991) 32
Li, Y.Q., see Zhao 107 (1991) 699
Liedenbaum, C.T.H.F., see Valster 107 (1991) 403
Lienert, U., see Böhrer 107 (1991) 555
Lin, P.S.D., see Colas 107 (1991) 243
Lin, P.S.D., see Bhat 107 (1991) 871
Lingunis, E.H., see Karam 107 (1991) 129
Liu, H., J.C. Roberts, J. Ramdani, S.M. Bedair, J. Farari, J.P. Vilcot and D. Decoster, A new approach for the integration of optoelectronic devices using laser selective area epitaxy 107 (1991) 878
Logan, R.A., see Tanbun-Ek 107 (1991) 751
Lootens, D., see Demeester 107 (1991) 161
Lorans, D., see Desjonquères 107 (1991) 626
Lowney, C., see Glew 107 (1991) 784
Li, Y., see Tang 107 (1991) 263
Lu, Z.H., see Hanna 107 (1991) 279
Lückerath, R., see Richter 107 (1991) 13
Lückerath, R., see Wisser 107 (1991) 111
Lum, R.M. and J.K. Klingert, Alternative Group V precursors for CVD applications 107 (1991) 290
Lundqvist, L., see Paska 107 (1991) 845
Lüth, H., see Kamp 107 (1991) 1053

Ma, K.Y., Z.M. Fang, R.M. Cohen and G.B. Stringfellow, OMVPE growth and characterization of Bi-containing III–V alloys 107 (1991) 416
Maa, B.Y., see Dapkus 107 (1991) 73
Machajdik, D., see Souc 107 (1991) 710
MacMillan, H.F., see Chung 107 (1991) 89
Majerfeld, A., see Hanna 107 (1991) 279
Makimoto, T., see Kobayashi 107 (1991) 62
Manabe, K., see Hiramatsu 107 (1991) 509
Mao, B.-Y., see Thomspon 107 (1991) 921
Mao, E.W., see Hanna 107 (1991) 279
Marfaing, Y., see Desjonquères 107 (1991) 626
Marks, T.J., see Zhang 107 (1991) 705
Marks, T.J., see Wills 107 (1991) 712
Marsh, E.M., see Cole 107 (1991) 254
Martin, B.G., see André 107 (1991) 855
Martin, E., see Aina 107 (1991) 932
Martin, G., see Thompson 107 (1991) 921
Martin, R.W., see Haywood 107 (1991) 422
Martin, T., C.R. Whitehouse and P.A. Lane, Growth mechanism studies in CBE/MOMBE 107 (1991) 969
Maruo, S., see Fujita 107 (1991) 644
Marx, D., see Musolf 107 (1991) 1043
Masato, H., see Suemune 107 (1991) 679
Mason, N.J. and P.J. Walker, Influence of gas mixing and expansion in horizontal MOVPE reactors 107 (1991) 181
Mason, N.J., see Haywood 107 (1991) 422
Mason, N.J., see Bougnot 107 (1991) 502
Mason, N.J., see Lakrimi 107 (1991) 518
Mastrovito, A., see Karam 107 (1991) 591
Mattingly, M., see Aina 107 (1991) 932
Maung, N., see Thompson 107 (1991) 860
Maurel, Ph., Ph. Bove, J.C. Garcia, J.P. Hirtz and M. Razeghi, MOMBE growth of high quality GaAs/GaInP heterostructures 107 (1991) 1076
McCormick, T., see Hanna 107 (1991) 279
McDermott, B.T., N.A. El-Masry, B.L. Jiang, F. Hyuga, S.M. Bedair and W.M. Duncan, Ordered GaInP by atomic layer epitaxy 107 (1991) 96
McKee, M.A., P.E. Norris, R.A. Stall, G.S. Tompa, C.S. Chern, D. Noh, S.S. Kang and T.J. Jasinski, Growth of highly uniform, reproducible InGaAs films in a multiwafer rotating disk reactor by MOCVD 107 (1991) 445
McQueen, A.E.D., P.N. Culshaw, J.C. Walton, D.V. Shenai-Khatkhate, D.J. Cole-Hamilton and J.B. Mullin, Synthesis and decomposition studies of dialkyltellurides of type RTeR′ 107 (1991) 325
Meddeb, J., see Draïdia 107 (1991) 483
Meguro, T., see Iwai 107 (1991) 136
Menocal, S.G., see Bhat 107 (1991) 772
Miklis, A., see Heinecke 107 (1991) 1062
Miner, C.J., see Knight 107 (1991) 221
Mircea, A., see Ougazzaden 107 (1991) 761
Mise, K., see Uchida 107 (1991) 1055
Mitsui, K., see Nishimura 107 (1991) 468
Miyamoto, N., see Suemitsu 107 (1991) 1015
Miyashita, M., see Nishimura 107 (1991) 468
Miyoshi, T., see Iwai 107 (1991) 136
Mizuguchi, K., see Kimura 107 (1991) 827
Moerman, I., see Demeester 107 (1991) 161

Moerman, I., G. Coudenys, P. Demeester, B. Turner and J. Crawley, Influence of gas mixing on the lateral uniformity in horizontal MOVPE reactors 107 (1991) 175
Molassioti, A., see Scholz 107 (1991) 365
Monteil, Y., see Abraham 107 (1991) 26
Montie, E.A., see Thijs 107 (1991) 731
Morello, G., see Genova 107 (1991) 1065
Morhaïm, C., see Mpaskoutas 107 (1991) 192
Mori, Y., see Taira 107 (1991) 952
Morio, K., see Yodo 107 (1991) 659
Morizuka, K., see Ashizawa 107 (1991) 903
Mörsch, G., see Kamp 107 (1991) 1053
Moseley, A.J., see Thompson 107 (1991) 860
Moser, M., see Scholz 107 (1991) 365
Moss, R.H., see Cole 107 (1991) 254
Motzkus, M., see Richter 107 (1991) 13
Mountziaris, T.J., see Jensen 107 (1991) 1
Mpaskoutas, M., C. Morhaïm, J.N. Patillon, J.P. André, A. Valster and J.J. Rusch, Uniformity – optical properties of GaInP–GaAlInP layers grown by MOVPE 107 (1991) 192
Muhr, G.T., see Bohling 107 (1991) 1068
Mullin, J.B., see McQueen 107 (1991) 325
Munns, G.O., see Woelk 107 (1991) 1074
Murawala, P.A., see Fujita 107 (1991) 644
Murotani, T., see Nishimura 107 (1991) 468
Murotani, T., see Kimura 107 (1991) 827
Murrell, A.J., see Foord 107 (1991) 1040
Musolf, J., D. Marx, A. Kohl, M. Weyers and P. Balk, Doping of GaAs and InP in MOMBE using DEZn, TESn and DETe 107 (1991) 1043

Nakajima, K., see Kondo 107 (1991) 578
Nakamura, F., see Taira 107 (1991) 952
Nakanishi, K., see Suemune 107 (1991) 679
Nakano, J., see Yamamoto 107 (1991) 796
Nelson, C.R., see Tompa 107 (1991) 198
Neumann, R., see Tews 107 (1991) 947
Nguyen Duy, T., see Smith 107 (1991) 605
Nicholas, R.J., see Haywood 107 (1991) 422
Nicholas, R.J., see Lakrimi 107 (1991) 518
Nicolas, J.L., see Frijlink 107 (1991) 166
Niggebrügge, U., see Kayser 107 (1991) 141
Nishikawa, H., see Soga 107 (1991) 479
Nishimura, T., K. Kadoiwa, N. Hayafuji, M. Miyashita, K. Mitsui, H. Kumabe and T. Murotani, Surface morphology improvement of GaAs-on-Si using a two-reactor MOCVD system and an AlAs/GaAs low temperature buffer layer: an approach to crack-free GaAs-on-Si 107 (1991) 468
Noda, S., see Takeda 107 (1991) 351
Noda, T., see Ashizawa 107 (1991) 903
Noh, D.W., see McKee 107 (1991) 445
Noh, D.W., see Zhao 107 (1991) 699
Nordell, N., B. Willén, C.-O.A. Olsson, U. Westergren and G. Landgren, Growth and performance of AlGaAs/GaAs heterostructure bipolar transistors 107 (1991) 909
Norman, A.G., see Glew 107 (1991) 784
Norris, P.E., see McKee 107 (1991) 445
Norris, P.E., see Zhao 107 (1991) 699
Notheisen, B., see Scholz 107 (1991) 365
Nowitzki, A., see Laube 107 (1991) 156

Obara, M., see Ashizawa 107 (1991) 903
O'Hare, D., see Foord 107 (1991) 1040
Oh, E.G., see Hanna 107 (1991) 279
Ohashi, Y., see Kato 107 (1991) 832
Ohkubo, M., see Tanaka 107 (1991) 898
Ohno, T. and T. Taguchi, The effects of photo-assisted MOCVD on the doping of Na acceptors into ZnS epitaxial layers 107 (1991) 649
Ohori, T., see Takikawa 107 (1991) 942
Ohtsuka, N., see Ozeki 107 (1991) 102
Oishi, M., see Yamamoto 107 (1991) 796
Ojala, P., see Landgren 107 (1991) 573
Okamoto, A., see Furuhata 107 (1991) 1049
Okamoto, T., see Yoshikawa 107 (1991) 653
Okuno, Y., see Asahi 107 (1991) 1009
Olsson C.-O.A., see Paska 107 (1991) 845
Olsson, C.-O.A., see Nordell 107 (1991) 909
Olsson, N.A., see Tanbun-Ek 107 (1991) 751
Onuma, K., A. Kasahara, K. Kato, N. Aihara and T. Udagawa, Atmospheric-pressure MOVPE growth of InP using Lewis base monovalent cyclopentadienyl indium 107 (1991) 360
Opitz, B., see Kayser 107 (1991) 141
Optiz, B., see Finders 107 (1991) 151
Osinski, J.S., see Grodzinski 107 (1991) 583
Ossart, P., see Draïdia 107 (1991) 483
Ougazzaden, A., J.-D. Ganière, Y. Gao, E.V.K. Rao, B. Sermage, C. Kazmierski and A. Mircea, Low threshold 1.5 μm SCH-MQW lasers by atmospheric pressure MOVPE and direct comparison of low versus atmospheric pressure MOVPE laser growth 107 (1991) 761
Ozeki, M., N. Ohtsuka, Y. Sakuma and K. Kodama, Pulsed jet epitaxy of III–V compounds 107 (1991) 102

Packeiser, G., H. Tews and P. Zwicknagl, High frequency AlGaAs/GaAs heterojunction bipolar transistors: the role of MOVPE 107 (1991) 883
Pagès, O., M. Renucci, O. Briot, N. Tempier and R.L. Aulombard, Raman characterization of ZnSe/GaAs MOVPE heterostructures 107 (1991) 670

Pain, G.N., C. Sandford, G.K.G. Smith, A.W. Stevenson, D. Gao, L.S. Wielunski, S.P. Russo, G.K. Reeves and R. Elliman, Low temperature MOCVD of $Hg_{1-x}Cd_xTe$ on 311, 511, 711 and shaped GaAs 107 (1991) 610
Pain, G.N., C.J. Rossouw, S.R. Glanvill, R.S. Rowe, R.S. Dickson, G.B. Deacon and B.O. West, HRTEM studies of defects and interdiffusion in $Hg_{1-x-y}Mn_yCd_xTe$ ($0 \le x,\ y \le 1$) grown by low temperature MOCVD 107 (1991) 632
Palevski, A., see Kuech 107 (1991) 116
Papadopoulo, A.C., see Draïdia 107 (1991) 483
Parker, C.A., see Gong 107 (1991) 83
Pascal, F., see Bougnot 107 (1991) 502
Paska, Z.F., J.Y. Andersson, L. Lundqvist and C.-O.A. Olsson, Growth and characterization of AlGaAs/GaAs quantum well structures for the fabrication of long wavelength infrared detectors 107 (1991) 845
Patel, D., see Smith 107 (1991) 605
Patillon, J.N., see Mpaskoutas 107 (1991) 192
Patillon, J.N., see André 107 (1991) 855
Patnaik, S., K.F. Jensen and K.P. Giapis, MOVPE of ZnSe using organometallic allyl selenium precursors 107 (1991) 390
Paulsson, G., see Samuelson 107 (1991) 68
Paulsson, G., see Jönsson 107 (1991) 1047
Pearton, S.J., see Bohling 107 (1991) 1068
Pemble, M.E., D.S. Buhaenko, S.M. Francis, P.A. Goulding and J.T. Allen, Surface science studies of MOVPE processes: a review of progress 107 (1991) 37
Peña-Sierra, R., J.G. Castro-Zavala and A. Escobosa, Growth of GaAs by MOCVD using a solid arsenic source 107 (1991) 337
Pennycook, S., see Karam 107 (1991) 591
Penz, R., see Ebbinghaus 107 (1991) 840
Pessa, M., see Tappura 107 (1991) 1070
Pinzone, C.J., see Dupuis 107 (1991) 790
Pistol, M.-E., A. Gustafsson, M. Gerling, L. Samuelson and H. Titze, MOVPE growth and characterization of strained layers 107 (1991) 458
Pistol, M.-E., see Titze 107 (1991) 513
Pohl, L., M. Hostalek, H. Schumann, U. Hartmann, W. Wassermann, A. Brauers, G.K. Regel, R. Hövel, P. Balk and F. Scholz, Physical properties of non-pyrophoric group III precursors for MOVPE 107 (1991) 309
Pohl, L., see Hövel 107 (1991) 355
Pohl, L., see Scholz 107 (1991) 365
Posthill, J.B., see Venkatasubramanian 107 (1991) 489
Potemski, R.M., see Kuech 107 (1991) 116
Potemski, R.M., see Tischler 107 (1991) 268
Potemski, R.M., see Buchan 107 (1991) 331
Pütz, N., InP based optoelectronics 107 (1991) 806
Quinn, W.E., D.E. Aspnes and S. Gregory, Applications of spectroellipsometry to the growth of GaAs and AlGaAs by metalorganic molecular beam epitaxy 107 (1991) 1045
Rakennus, K., see Tappura 107 (1991) 1070
Ramdani, J., see Liu 107 (1991) 878
Rao, E.V.K., see Ougazzaden 107 (1991) 761
Razeghi, M., see Maurel 107 (1991) 1076
Reeves, G.K., see Pain 107 (1991) 610
Regel, G.K., see Pohl 107 (1991) 309
Reier, F.W., see Wolf 107 (1991) 381
Reier, F.W., P. Harde and H. Kaiser, LP-MOVPE growth and characterization of wide-gap InGaAs/InP layers ($\lambda_g < 1.2$ μm) for optical waveguide applications 107 (1991) 867
Reinhardt, F., see Schwedler 107 (1991) 531
Reinhardt, F., see Hergeth 107 (1991) 537
Reinhardt, F., see Camassel 107 (1991) 543
Remiens, D., see Rose 107 (1991) 850
Renaud, M., see Ackaert 107 (1991) 822
Renucci, M., see Pagès 107 (1991) 670
Richeson, D.S., see Zhang 107 (1991) 705
Richter, W., P. Kurpas, R. Lückerath, M. Motzkus and R. Waschbüsch, Gas phase studies of MOVPE by optical methods 107 (1991) 13
Richter, W., see Wisser 107 (1991) 111
Riglet, P., see André 107 (1991) 855
Robein, D., see Rose 107 (1991) 850
Roberts, J.C., see Liu 107 (1991) 878
Roberts, J.S., K.C. Singh, C.C. Button, J.P.R. David and J. Woodhead, AlGaAs/GaAs p-MODFET materials grown using intrinsic carbon doping 107 (1991) 915
Roentgen, P., see Galeuchet 107 (1991) 147
Roentgen, P., W. Heuberger, G.L. Bona and P. Unger, MOVPE of AlGaInP/GaInP heterostructures for visible lasers 107 (1991) 724
Rose, B., D. Remiens, V. Hornung and D. Robein, Application of AP MOVPE to a new butt-coupling scheme 107 (1991) 850
Rosenzweig, M., W. Ebert, D. Franke, N. Grote, B. Sartorius and P. Wolfram, Lasing characteristics of InGaAs/InGaAsP MQW structures grown by low-pressure MOVPE 107 (1991) 802
Rossouw, C.J., see Pain 107 (1991) 632
Roth, B., see Gyuro 107 (1991) 956
Rothwell, W.J.M., see Cole 107 (1991) 254
Rowe, R.S., see Pain 107 (1991) 632
Rudra, A., see Carlin 107 (1991) 1057
Rusch, J.J., see Mpaskoutas 107 (1991) 192
Rushworth, S.A., see Jones 107 (1991) 350
Russo, S.P., see Pain 107 (1991) 610
Saito, H., see Fukui 107 (1991) 231
Saka, T., see Kato 107 (1991) 832

Sakuma, Y., see Ozeki 107 (1991) 102
Salagaj, T., see Tompa 107 (1991) 198
Salokatve, A., see Tappura 107 (1991) 1070
Samuelson, L., K. Deppert, S. Jeppesen, J. Jönsson, G. Paulsson and P. Schmidt, Reflectance-difference study of surface chemistry in MOVPE growth 107 (1991) 68
Samuelson, L., see Pistol 107 (1991) 458
Samuelson, L., see Titze 107 (1991) 513
Samuelson, L., see Jönsson 107 (1991) 1047
Sandford, C., see Pain 107 (1991) 610
Sandhu, A., see Fujii 107 (1991) 1030
Sartorius, B., see Rosenzweig 107 (1991) 802
Sasaki, A., see Takeda 107 (1991) 351
Scheffer, F., see Guimarães 107 (1991) 434
Scheffer, F., see Lakner 107 (1991) 452
Scheffer, F., see Gyuro 107 (1991) 956
Scherg, T., see Ebbinghaus 107 (1991) 840
Schiavone, L., see Colas 107 (1991) 243
Schmidt, P., see Samuelson 107 (1991) 68
Schmidt, P., K. Deppert and H. Kostial, Silicon spike-doping of GaAs with AP-MOVPE 107 (1991) 259
Schmidt, P., see Jönsson 107 (1991) 1047
Schmitz, D., G. Strauch, H. Jürgensen and M. Heyen, Growth of extremely uniform III–V compound semiconductor layers by LP-MOVPE by application of the gas foil technique for substrate rotation 107 (1991) 188
Schneider, K., see Kayser 107 (1991) 141
Schnell, R.D., see Tews 107 (1991) 947
Scholz, F., see Pohl 107 (1991) 309
Scholz, F., A. Molassioti, M. Moser, B. Notheisen, K. Streubel, M. Hostalek and L. Pohl, Novel liquid precursors for the growth of InP and GaInAs epitaxial layers by MOVPE 107 (1991) 365
Schreiber, M., see Korte 107 (1991) 779
Schumann, H., see Pohl 107 (1991) 309
Schumann, H., see Wolf 107 (1991) 381
Schütze, A., see Zacheja 107 (1991) 314
Schütze, A., J. Zacheja, M. Weyers and D. Kohl, Surface chemistry of a new III–V MOCVD reactant: $PhAsH_2$ on GaAs(100) 107 (1991) 1036
Schwarz, S.A., see Bhat 107 (1991) 772
Schwarz, S.A., see Bhat 107 (1991) 871
Schwedler, R., F. Reinhardt, D. Grützmacher and K. Wolter, Temperature resolved photoluminescence investigations on InGaAs/InP MQWs 107 (1991) 531
Scilla, G., see Tischler 107 (1991) 268
Scott, E.G., see Davies 107 (1991) 999
Sell, H.-J., Growth of GaInAs bulk mixed crystals as a substrate with a tailored lattice parameter 107 (1991) 396
Sergent, A.M., see Tanbun-Ek 107 (1991) 751
Serio, M., see Aina 107 (1991) 932
Sermage, B., see Draïdia 107 (1991) 483
Sermage, B., see Ougazzaden 107 (1991) 761
Severens, A.L.G., see Valster 107 (1991) 403
Shahar, A., see Colas 107 (1991) 226
Shenai-Khatkhate, D.V., see McQueen 107 (1991) 325
Sherwin, M.E., see Woelk 107 (1991) 1074
Shiba, Y., see Fujita 107 (1991) 473
Shibata, S., see Kato 107 (1991) 832
Shichi, E., see Kato 107 (1991) 832
Shimawaki, H., see Furuhata 107 (1991) 1049
Shimoyama, K., Y. Inoue, M. Katoh, H. Gotoh, Y. Suzuki and H. Yajima, A new selective MOVPE regrowth process utilizing in-situ vapor phase etching for optoelectronic integrated circuits 107 (1991) 767
Shiohara, Y., see Sugimoto 107 (1991) 692
Simhony, S., see Colas 107 (1991) 243
Simhony, S., see Bhat 107 (1991) 716
Simmons, M.Y., P.D. Brown and K. Durose, MOVPE growth and characterisation of CdTe on CdS single crystal substrates 107 (1991) 664
Singh, K.C., see Roberts 107 (1991) 915
Singh, N.K., see Foord 107 (1991) 1040
Singh, S., see Dupuis 107 (1991) 790
Skevington, P.J., see Cole 107 (1991) 254
Skevington, P.J., see Davies 107 (1991) 999
Smatko, V., see Souc 107 (1991) 710
Smith, G.K.G., see Pain 107 (1991) 610
Smith, H.I., see Karam 107 (1991) 591
Smith, L.M., C.F. Byrne, D. Patel, P. Knowles, J. Thompson, G.T. Jenkin, T. Nguyen Duy, A. Durand and M. Bourdillot, The growth of CMT on GaAs for high quality linear arrays of MWIR and LWIR photodiodes 107 (1991) 605
Soga, T., H. Nishikawa, T. Jimbo and M. Umeno, Very low dislocation density GaAs on Si using superlattices grown by MOCVD 107 (1991) 479
Soga, T., see Egawa 107 (1991) 757
Solomon, P., see Kuech 107 (1991) 116
Soole, B.D., see Colas 107 (1991) 226
Souc, J., D. Machajdik, V. Smatko, V. Strbik, K. Fröhlich, S. Hrib, S. Stefanik, P. Kordos and J. Ivan, Preparation and properties of Ba-deficient superconducting thin Y–Ba–Cu–O films 107 (1991) 710
Soulière, V., see Abraham 107 (1991) 26
Speier, P., see Laube 107 (1991) 156
Speier, P., see Wiedemann 107 (1991) 561
Spiller, G.D.T., see Cole 107 (1991) 254
Spurdens, P.C., M.R. Taylor, M. Hockly and M.J. Yates, The influence of growth conditions on the planarity of MOVPE grown GaInAs(P) interfaces 107 (1991) 215
Staehli, A., see Carlin 107 (1991) 1057
Stagg, J.P., see Glew 107 (1991) 784

Stall, R.A., see Tompa 107 (1991) 198
Stall, R.A., see McKee 107 (1991) 445
Stefanik, S., see Souc 107 (1991) 710
Stevenson, A.W., see Pain 107 (1991) 610
Stoffel, N.G., see Bhat 107 (1991) 716
Strauch, G., see Schmitz 107 (1991) 188
Strbik, V., see Souc 107 (1991) 710
Streubel, K., see Scholz 107 (1991) 365
Stringfellow, G.B., see Li 107 (1991) 32
Stringfellow, G.B., see Ma 107 (1991) 416
Stringfellow, G.B., see Lakrimi 107 (1991) 518
Strzoda, R., see Ebbinghaus 107 (1991) 840
Suchet, P., see Frijlink 107 (1991) 166
Studna, S.S., see Colas 107 (1991) 47
Sudo, H., see Yamamoto 107 (1991) 796
Suemitsu, M., F. Hirose and N. Miyamoto, Si and Ge gas-source molecular beam epitaxy (GSMBE) 107 (1991) 1015
Suemune, I., H. Masato, K. Nakanishi, Y. Kuroda and M. Yamanishi, Doping of nitrogen in ZnSe films: improved doping properties in ZnSe/ZnSSe periodic layered structures grown on GaAs by MOVPE 107 (1991) 679
Suemune, I., K. Hamaoka, A. Kishimoto, T. Koui, Y. Honda and M. Yamanishi, Hydrogen-plasma and photo-effects on MOMBE of GaAs 107 (1991) 1041
Sugawara, K., see Sugimoto 107 (1991) 692
Sugimoto, T., M. Yoshida, K. Yamaguchi, Y. Yamada, K. Sugawara, Y. Shiohara and S. Tanaka, Fabrication and characterization of Bi–Sr–Ca–Cu–O MOCVD thin films 107 (1991) 692
Sugiyama, Y., see Fujii 107 (1991) 1030
Summers, G., see Lakrimi 107 (1991) 518
Susawa, H., see Kato 107 (1991) 832
Suzuki, M., see Takikawa 107 (1991) 942
Suzuki, Y., see Shimoyama 107 (1991) 767
Szmyd, D.M., see Hanna 107 (1991) 279

Tada, H., see Egawa 107 (1991) 757
Taguchi, T., see Ohno 107 (1991) 649
Taira, K., F. Nakamura, I. Hase, H. Kawai and Y. Mori, InAs–GaSb hot electron transistors grown by metalorganic chemical vapor deposition 107 (1991) 952
Takechi, M., see Takikawa 107 (1991) 942
Takeda, Y., S. Araki, M. Takemi, S. Noda and A. Sasaki, Growth of GaInP over the whole composition range by OMVPE using tertiarybutylphosphine for the phosphorus source 107 (1991) 351
Takemi, M., see Takeda 107 (1991) 351
Takikawa, M., T. Ohori, M. Takechi, M. Suzuki and J. Komeno, Pseudomorphic n-InGaP/InGaAs/GaAs grown by MOVPE for HEMT LSIs 107 (1991) 942
Tanahashi, T., see Kondo 107 (1991) 578
Tanaka, H., see Kikkawa 107 (1991) 370
Tanaka, S., see Yodo 107 (1991) 659
Tanaka, S., see Sugimoto 107 (1991) 692
Tanaka, S., M. Ohkubo, M. Irikawa and T. Kikuta, MOVPE growth of highly zinc-doped bases for GaAs/AlGaAs heterojunction bipolar transistors 107 (1991) 898
Tanbun-Ek, T., R.A. Logan, H. Temkin, N.A. Olsson, M.C. Wu, A.M. Sergent and K.W. Wecht, Reproducible growth of narrow line-width multiple quantum well graded index separate confinement distributed feedback (MQW-GRIN-SCH-DFB) lasers by MOVPE 107 (1991) 751
Tang, X., J. te Nijenhuis, Y. Li and L.J. Giling, The influence of substrate orientation and mis-orientation on the Si-doping of GaAs grown by MOVPE 107 (1991) 263
Tanner, Ch., see Korte 107 (1991) 779
Tappura, K., A. Salokatve, K. Rakennus, H. Asonen and M. Pessa, The substrate–epitaxial interface of GaAs and InP grown by GSMBE 107 (1991) 1070
Taylor, M.R., see Spurdens 107 (1991) 215
Te Nijenhuis, J., see Tang 107 (1991) 263
Te Nijenhuis, J., P.J. van der Wel, R.W.F. van Asten, P.R. Hageman and L.J. Giling, Critical layer thickness of MOVPE-grown GaAs on $In_xGa_{1-x}As$ 107 (1991) 496
Temkin, H., see Tanbun-Ek 107 (1991) 751
Tempier, N., see Pagès 107 (1991) 670
Terada, T., see Fujita 107 (1991) 621
Tews, H., see Packeiser 107 (1991) 883
Tews, H., R. Neumann and R.D. Schnell, Growth and characterization of double barrier resonant tunnelling diodes 107 (1991) 947
Thibierge, H., see Benchimol 107 (1991) 978
Thijs, P.J.A., E.A. Montie and T. van Dongen, Structures for improved 1.5 μm wavelength lasers grown by LP-OMVPE; In GaAs–InP strained-layer quantum wells a good candidate 107 (1991) 731
Thompson, A.G., H.M. Levy, B.-Y. Mao, G. Martin and G.Y. Lee, MOVPE grown high performance 0.25 μm AlGaAs/InGaAs/GaAs pseudomorphic MODFETs 107 (1991) 921
Thompson, J., see Smith 107 (1991) 605
Thompson, J., A.K. Wood, A.J. Moseley, M.Q. Kearley, P.J. Topham, N. Maung and N. Carr, The use of InP-based semiconductor reflective stacks for enhanced device performance 107 (1991) 860

Thrush, E.J., see Cureton 107 (1991) 549
Timmons, M.L., see Venkatasubramanian 107 (1991) 489
Tischler, M.A., see Kuech 107 (1991) 116
Tischler, M.A., R.M. Potemski, T.F. Kuech, F. Cardone, M.S. Goorsky and G. Scilla, Acceptor doping of (Al,Ga)As using carbon by metalorganic vapor phase epitaxy 107 (1991) 268
Tischler, M.A., see Buchan 107 (1991) 331
Titze, H., see Pistol 107 (1991) 458
Titze, H., M. Gerling, M.-E. Pistol and L. Samuelson, MOVPE growth of GaP and $GaAs_xP_{1-x}$ on (111)-oriented GaP 107 (1991) 513
Tomlinson, W.J., see Colas 107 (1991) 226
Tompa, G.S., T. Salagaj, L. Cook, R.A. Stall, C.R. Nelson, P.L. Anderson, W.H. Wright, W.L. Ahlgren and S.M. Johnson, MOVPE growth of II–VI compounds in a vertical reactor with high-speed horizontal rotating disk 107 (1991) 198
Tompa, G.S., see McKee 107 (1991) 445
Tonge, L.M., see Wills 107 (1991) 712
Topham, P.J., see Thompson 107 (1991) 860
Toyoda, T., see Kawakami 107 (1991) 1072
Treichler, R., see Korte 107 (1991) 779
Triboulet, R., MOVPE of narrow band gap II–VI materials 107 (1991) 598
Triboulet, R., see Desjonquères 107 (1991) 626
Tromson-Carli, A., see Desjonquères 107 (1991) 626
Tsai, C.S., see Kuech 107 (1991) 116
Tsang, W.T., Current status review and future prospects of CBE, MOMBE and GSMBE 107 (1991) 960
Tsugami, M., see Kimura 107 (1991) 827
Tsuzuki, N., see Yamamoto 107 (1991) 796
Turner, B., see Moerman 107 (1991) 175

Uchida, T., see Uchida 107 (1991) 1055
Uchida, T.K., T. Uchida, K. Mise, N. Yokouchi, F. Koyama and K. Iga, CBE growth of GaInAs–InP wafers for surface emitting lasers 107 (1991) 1055
Udagawa, T., see Onuma 107 (1991) 360
Ueda, K., see Yodo 107 (1991) 659
Uesugi, F., see Kimura 107 (1991) 827
Umeno, M., see Soga 107 (1991) 479
Umeno, M., see Egawa 107 (1991) 757
Unger, P., see Roentgen 107 (1991) 724
Usagawa, T., see Hiruma 107 (1991) 440

Vahala, K.J., see Kuech 107 (1991) 116
Valster, A., see Mpaskoutas 107 (1991) 192
Valster, A., C.T.H.F. Liedenbaum, M.N. Finke, A.L.G. Severens, M.J.B. Boermans, D.E.W. Vandenhoudt and C.W.T. Bulle-Lieuwma, High quality $Al_xGa_{1-x-y}In_yP$ alloys grown by MOVPE on (311)B GaAs substrates 107 (1991) 403
Van Asten, R.W.F., see Te Nijenhuis 107 (1991) 496
Van Daele, P., see Demeester 107 (1991) 161
Van Daele, P., see Ackaert 107 (1991) 822
Van der Gaag, B., see Colas 107 (1991) 243
Van der Wel, P.J., see Te Nijenhuis 107 (1991) 496
Van der Ziel, J.P., see Dupuis 107 (1991) 790
Van Dongen, T., see Thijs 107 (1991) 731
Vandenhoudt, D.E.W., see Valster 107 (1991) 403
Venkatasubramanian, R., M.L. Timmons, J.B. Posthill, B.M. Keyes and R.K. Ahrenkiel, High quality GaAs on Si using $Si_{0.04}Ge_{0.96}$/Ge buffer layers 107 (1991) 489
Vernon, S.M., see Karam 107 (1991) 129
Vilcot, J.P., see Liu 107 (1991) 878

Walker, P.J., see Mason 107 (1991) 181
Walker, P.J., see Haywood 107 (1991) 422
Walker, P.J., see Bougnot 107 (1991) 502
Walker, P.J., see Lakrimi 107 (1991) 518
Walton, J.C., see McQueen 107 (1991) 325
Waschbüsch, M., see Wisser 107 (1991) 111
Waschbüsch, R., see Richter 107 (1991) 13
Wassermann, W., see Pohl 107 (1991) 309
Watanabe, N., see Böhrer 107 (1991) 555
Watkins, S.P., see Haacke 107 (1991) 342
Watt, B., see Knight 107 (1991) 221
Wayman, C.M., see York 107 (1991) 741
Wecht, K.W., see Tanbun-Ek 107 (1991) 751
Wee, A.T.S., see French 107 (1991) 1038
Wee, A.T.S., see Foord 107 (1991) 1040
Weimann, G., see Korte 107 (1991) 779
Weinmann, R., see Wiedemann 107 (1991) 561
Wendt, J.R., see Biefeld 107 (1991) 836
Wessels, B.W., see Zhang 107 (1991) 705
Wessels, B.W., see Wills 107 (1991) 712
West, B.O., see Pain 107 (1991) 632
Westergren, U., see Nordell 107 (1991) 909
Westphalen, B., see Kayser 107 (1991) 141
Weyers, M., see Finders 107 (1991) 151
Weyers, M., New starting materials for MOMBE 107 (1991) 1021
Weyers, M., see Schütze 107 (1991) 1036
Weyers, M., see Musolf 107 (1991) 1043
Weyers, M., see Kamp 107 (1991) 1053
Whitaker, T.J., see Foord 107 (1991) 1040
Whiteaway, J.E.A., see Glew 107 (1991) 784
Whitehouse, C.R., see Martin 107 (1991) 969
Wiedemann, P., M. Klenk, W. Körber, U. Koerner, R. Weinmann, E. Zielinski and P. Speier, MOVPE of In(GaAs)P/In GaAs MQW structures 107 (1991) 561
Wielunski, L.S., see Pain 107 (1991) 610
Willén, B., see Nordell 107 (1991) 909
Williams, D.A., see Bottka 107 (1991) 893
Williams, J.O., see Yates 107 (1991) 386

Wills, L.A., W.A. Feil, B.W. Wessels, L.M. Tonge and T.J. Marks, Growth studies of ferroelectric oxide layers prepared by organometallic chemical vapor deposition 107 (1991) 712
Winterfeld, J., see Wolf 107 (1991) 381
Wisser, J., P. Czuprin, D. Grundmann, P. Balk, M. Waschbüsch, R. Lückerath and W. Richter, GaAs epitaxy using alternate pulses in a standard LP-MOVPE reactor 107 (1991) 111
Woelk, E., M.E. Sherwin and G.O. Munns, InGaAs MOMBE – system drift and material quality 107 (1991) 1074
Wolf, T., A. Krost, D. Bimberg, F. Reier, P. Harde, J. Winterfeld and H. Schumann, Transition metal doping of LP-MOCVD-grown InP 107 (1991) 381
Wolfram, P., see Rosenzweig 107 (1991) 802
Wolter, K., see Schwedler 107 (1991) 531
Wolter, K., see Camassel 107 (1991) 543
Wood, A.K., see Thompson 107 (1991) 860
Woodhead, J., see Roberts 107 (1991) 915
Wright, P.D., see Bottka 107 (1991) 893
Wright, P.J., see Jones 107 (1991) 297
Wright, W.H., see Tompa 107 (1991) 198
Wu, M.C., see Tanbun-Ek 107 (1991) 751
Wu, Y.-H., see Kawakami 107 (1991) 1072

Yajima, H., see Shimoyama 107 (1991) 767
Yamada, Y., see Sugimoto 107 (1991) 692
Yamaguchi, K., see Sugimoto 107 (1991) 692
Yamamoto, M., M. Oishi, H. Sudo, J. Nakano and N. Tsuzuki, Strained-layer InGaAs/InGaAsP MQW structures and their application to 1.67 μm lasers grown by metalorganic vapor phase epitaxy 107 (1991) 796
Yamane, H., see Hirai 107 (1991) 683
Yamanishi, M., see Suemune 107 (1991) 679
Yamanishi, M., see Suemune 107 (1991) 1041
Yamashita, K., see Yodo 107 (1991) 659
Yamauchi, Y., see Kobayashi 107 (1991) 62
Yates, M.J., see Spurdens 107 (1991) 215
Yates, H.M., and J.O. Williams, Purity of zinc precursors and the properties of epitaxial ZnSe grown by atmospheric pressure metalorganic chemical vapour deposition 107 (1991) 386
Yi-Yan, A., see Bhat 107 (1991) 871
Yodo, T., K. Ueda, K. Morio, K. Yamashita and S. Tanaka, High quality over-epilayer growth of ZnSe on Li^+-implanted ZnSe epilayers by atmospheric pressure MOVPE 107 (1991) 659
Yokouchi, N., see Uchida 107 (1991) 1055
York, P.K., K.J. Beernink, J. Kim, J.J. Alwan, J.J. Coleman and C.M. Wayman, Metalorganic chemical vapor deposition of InGaAs–GaAs–AlGaAs strained-layer quantum well lasers 107 (1991) 741
Yoshida, M., see Sugimoto 107 (1991) 692
Yoshie, T., see Fujita 107 (1991) 674
Yoshikawa, A., T. Okamoto and T. Fujimoto, Effects of Ar ion laser irradiation on MOVPE of ZnSe using DMZn and DMSe as reactants 107 (1991) 653
Young, E.W.A. and G.M. Fontijn, On the "tunnel" diffusion of iron dopant in InP 107 (1991) 274
Yun Feng, see Gao 107 (1991) 428

Zacheja, J., A. Schütze, A. Brauers and D. Kohl, Detection of phenylarsine in air 107 (1991) 314
Zacheja, J., see Schütze 107 (1991) 1036
Zah, C.E., see Bhat 107 (1991) 772
Zah, C.E., see Bhat 107 (1991) 871
Zawadzki, P., see Zhao 107 (1991) 699
Zhang, J.M., B.W. Wessels, D.S. Richeson and T.J. Marks, Preparation and properties of superconducting Bi–Sr–Ca–Cu–O thin films on polycrystalline silver substrates by organometallic chemical vapor deposition 107 (1991) 705
Zhang Jikang, see Gao 107 (1991) 428
Zhao, J., C.S. Chern, Y.Q. Li, D.W. Noh, P.E. Norris, P. Zawadzki, B. Kear and B. Gallois, In-situ growth of YBCO high-T_c superconducting thin films by plasma-enhanced metalorganic chemical vapor deposition 107 (1991) 699
Zielinski, E., see Wiedemann 107 (1991) 561
Zimmer, M., R. Hövel, W. Brysch, A. Brauers and P. Balk, Trisdimethylaminoarsine as As source for the LP-MOVPE of GaAs 107 (1991) 348
Zimmer, M.H., see Hövel 107 (1991) 355
Zou, Y., see Grodzinski 107 (1991) 583
Zwicknagl, P., see Packeiser 107 (1991) 883
Zydzik, G.J., see Dupuis 107 (1991) 790

Journal of Crystal Growth 107 (1991) 1091–1094
North-Holland

Subject index

Adducts 297, 355, 365, 386, 989, 1040
Adsorption 37, 56, 263, 314, 1040
Aluminum
– arsenide 231, 479
– gallium arsenide 47, 83, 89, 116, 161, 175, 226, 237, 243, 268, 309, 350, 370, 428, 434, 452, 520, 591, 716, 757, 767, 779, 845, 883, 893, 903, 909, 915, 921, 947, 956, 982, 1030, 1040, 1045, 1068
– gallium indium phosphide 192, 403, 578, 724
– indium arsenide 932
– nitride 376
– organic 83, 89, 116, 175, 192, 226, 231, 309, 376, 403, 428, 434, 452, 479, 483, 555, 578, 591, 716, 724, 757, 767, 779, 784, 832, 845, 860, 883, 893, 898, 909, 915, 921, 932, 947, 956, 982, 1009, 1030, 1068
Antimony
– organic 181, 416, 422, 502, 836, 952, 1009
Apparatus
– for thin film growth
– – by chemical beam epitaxy
– – – of gallium arsenide 969
– – – of gallium indium arsenide 969
– – by hot wall epitaxy
– – – of gallium arsenide 331
– – by vapor phase epitaxy
– – – through metalorganic chemical vapor deposition
– – – – of bismuth strontium calcium cuprate 705
– – – – of ferroelectric oxides 712
– – – – of gallium arsenide 290, 468
– – – – of III–V compounds 166, 175, 192, 370
– – – – of II–VI compounds 202
– – – – of yttrium barium cuprate 683
– – – – zinc silicon diarsenide 410
– – – – photoassisted
– – – – – of mercury cadmium telluride 621
– for miscellaneous purposes
– – measuring vapor pressure 319
– – mixing of gases in CVD 181
– – reflectance difference spectroscopy 47
Arsenic
– organic 13, 32, 268, 281, 290, 314, 342, 348, 370, 422, 644, 1009, 1021, 1036, 1041

Barium
– organic 683, 699, 710
Bismuth
– organic 416, 683, 692, 705, 712
– strontium calcium cuprate 683, 692, 705
– titanate 712

Cadmium
– mercury telluride 297, 598, 605, 610, 621, 626, 632
– organic 254, 297, 605, 621, 626, 632, 674
– telluride 664
Calcium
– organic 683, 692, 705
Characterization methods
– by absorption spectroscopy 319, 531, 543, 555, 621, 845
– by Auger electron spectroscopy 37, 428, 483, 699, 921, 1015
– by cathodoluminescence 147, 243, 458, 483, 509
– by electrical methods 83, 89, 116, 141, 166, 188, 209, 248, 254, 259, 263, 279, 290, 314, 331, 337, 342, 348, 350, 355, 360, 365, 370, 376, 381, 386, 390, 403, 410, 422, 428, 434, 440, 445, 489, 502, 561, 598, 605, 621, 644, 670, 683, 699, 710, 724, 731, 741, 751, 757, 761, 767, 772, 784, 790, 796, 802, 806, 827, 832, 836, 840, 850, 855, 878, 883, 893, 898, 903, 909, 915, 921, 926, 932, 942, 947, 952, 956, 960, 978, 982, 1009, 1030, 1943, 1049, 1053, 1055, 1057, 1070, 1074, 1076
– by electroluminescence 509
– by electron microscopy 96, 116, 129, 141, 147, 156, 161, 203, 215, 226, 231, 237, 243, 259, 274, 376, 390, 403, 428, 445, 452, 468, 473, 479, 483, 489, 494, 496, 502, 509, 520, 549, 561, 583, 591, 598, 610, 626, 632, 659, 664, 683, 692, 705, 710, 712, 716, 741, 751, 761, 767, 772, 784, 790, 822, 840, 850, 860, 871, 903, 921, 956, 989, 999, 1049
– by electron probe microanalysis 978
– by electron spin resonance 325
– by ellipsometry 1045
– by emission 161, 621, 741, 751, 757
– by Fourier transform infrared 416, 605, 845, 860
– by inductively coupled plasma spectrometry 496
– by infrared spectroscopy 37, 248, 621
– by low energy electron diffraction 37
– by magnetic properties 422
– by mass spectrometry 32, 290, 314, 360, 969, 982, 1036, 1043, 1072
– by nuclear magnetic resonance 325
– by optical microscopy 83, 129, 337, 360, 416, 468, 513, 598, 610, 653, 692, 1049
– by optical properties 13, 37, 62, 434
– by photoluminescence 83, 96, 102, 129, 166, 175, 188, 192, 221, 237, 297, 342, 348, 350, 355, 360, 365, 370, 386, 403, 428, 434, 445, 452, 458, 489, 494, 496, 502, 513, 520, 531, 537, 543, 549, 555, 561, 567, 573, 578, 583, 591, 637, 649, 653, 659, 674, 679, 724, 731, 761, 767, 784, 796, 802, 822, 827, 845, 883, 947, 978, 1009, 1021, 1030, 1055, 1060, 1062, 1065, 1072, 1076

- by Raman spectroscopy 13, 26, 102, 111, 136, 151, 473, 670, 1009
- by reflectance difference spectroscopy 47, 68, 543, 653, 1047
- by reflection high energy electron diffraction 47, 360, 664, 1053, 1072
- by reflectivity 102, 410, 543, 790, 832, 860, 893
- by Rutherford back scattering 610
- by secondary ion mass spectrometry 156, 248, 268, 274, 381, 390, 440, 483, 626, 644, 761, 779, 836, 860, 867, 883, 898, 903, 909, 921, 932, 978, 982, 1021, 1068
- by transmission spectroscopy 518, 598
- by X-ray photoemission spectroscopy 73
- by X-ray methods 96, 102, 116, 166, 175, 192, 202, 221, 231, 268, 279, 351, 376, 390, 396, 403, 410, 416, 428, 483, 502, 520, 549, 555, 561, 567, 583, 598, 605, 610, 626, 632, 637, 653, 674, 683, 692, 699, 705, 710, 712, 751, 796, 822, 845, 855, 860, 867, 921, 926, 932, 978, 999, 1051, 1057, 1062, 1065, 1074, 1076

Copper
- organic 683, 692, 699, 705, 710

Devices 89, 116, 161, 166, 243, 290, 314, 410, 434, 518, 598, 605, 637, 716, 724, 731, 741, 751, 757, 761, 767, 772, 779, 784, 790, 802, 806, 822, 827, 832, 836, 840, 845, 850, 855, 860, 867, 871, 878, 883, 893, 903, 909, 915, 921, 926, 932, 942, 952, 956, 960, 1065

Diffusional control 166, 226, 259, 632, 779, 840, 909

Dislocations 458, 479, 489, 496, 692, 757

Dopants 89, 156, 188, 248, 254, 259, 263, 268, 274, 279, 360, 381, 428, 598, 632, 637, 679, 724, 772, 779, 836, 840, 878, 883, 903, 915, 942, 982, 1030, 1043, 1051, 1053

Etching
- chemical 141, 156, 161, 203, 226, 237, 410, 468, 473, 479, 494, 513, 583, 591, 605, 664, 670, 757, 822, 850, 942, 1072
- reactive ion 156, 161
- thermal 1072
- thermochemical 767

Ferroelectric oxides 712

Gallium
- aluminum arsenide 483, 832, 1021
- antimonide 181, 422, 952
- arsenide 1, 13, 26, 37, 47, 56, 62, 68, 73, 83, 102, 111, 116, 129, 136, 161, 166, 175, 188, 226, 231, 243, 248, 259, 263, 279, 281, 290, 309, 331, 337, 342, 348, 370, 428, 434, 440, 452, 458, 468, 473, 479, 483, 489, 496, 583, 591, 644, 716, 757, 767, 772, 822, 855, 878, 883, 893, 898, 903, 909, 915, 921, 926, 942, 947, 956, 969, 982, 999, 1021, 1036, 1041, 1043, 1045, 1047, 1049, 1051, 1053, 1070, 1076
- arsenide phosphide 458, 479, 513
- indium antimonide 502, 952
- indium arsenide 141, 147, 166, 365, 396, 520, 537, 543, 567, 850, 855, 969, 989, 1038, 1055, 1057, 1060
- indium arsenide phosphide 850, 978, 1021
- indium phosphide 96, 192, 351, 724, 1076
- nitride 376, 509
- organic 1, 12, 32, 37, 47, 68, 73, 83, 89, 111, 116, 136, 141, 175, 181, 192, 221, 226, 231, 248, 254, 259, 263, 274, 281, 309, 331, 337, 348, 350, 351, 365, 376, 403, 422, 428, 434, 440, 445, 452, 475, 479, 483, 489, 496, 502, 509, 513, 537, 555, 561, 567, 573, 578, 583, 591, 644, 716, 724, 731, 741, 751, 757, 761, 767, 772, 779, 784, 790, 796, 822, 827, 832, 840, 845, 855, 860, 867, 871, 878, 883, 893, 898, 903, 909, 915, 921, 926, 942, 947, 952, 956, 978, 982, 989, 999, 1009, 1030, 1041, 1049, 1051, 1053, 1055, 1057, 1060, 1062, 1065, 1068, 1074, 1076
- phosphide 102, 458, 513

Germanium 1015

Heterojunction 116, 141, 202, 215, 403, 422, 434, 440, 452, 489, 555, 573, 637, 670, 679, 724, 731, 741, 761, 767, 779, 790, 796, 802, 806, 827, 855, 871, 883, 893, 898, 903, 915, 921, 932, 942, 947, 978, 1072, 1076

Hydrodynamics 1, 445

Impurity 1, 342, 360, 376, 386, 390, 434, 644, 679, 915, 926, 932, 947, 969, 982, 1021, 1030, 1068, 1070, 1076

Indium
- aluminum arsenide 555
- antimonide 836
- arsenide 422, 952
- arsenide, bismuth containing 416
- arsenide antimonide 836
- arsenide antimonide, bismuth containing 416
- gallium aluminum arsenide 784, 806, 860
- gallium aluminum arsenide antimonide 1009
- gallium arsenide 116, 151, 175, 309, 370, 445, 531, 549, 555, 573, 583, 731, 741, 751, 784, 790, 796, 802, 840, 860, 871, 915, 921, 942, 999, 1065, 1074
- gallium arsenide phosphide 209, 215, 221, 549, 561, 751, 761, 796, 802, 806, 827, 860, 867, 871
- gallium phosphide 151, 942
- organic 116, 141, 156, 175, 221, 254, 274, 281, 309, 351, 355, 360, 365, 403, 416, 422, 445, 502, 537, 555, 561, 567, 573, 578, 583, 724, 731, 741, 751, 761, 772, 784, 790, 796, 827, 836, 840, 855, 860, 867, 871, 915, 921, 932, 942, 952, 978, 989, 999, 1009, 1038, 1055, 1057, 1060, 1062, 1074
- phosphide 13, 26, 156, 175, 188, 203, 254, 274, 309, 355, 360, 365, 381, 458, 494, 573, 716, 731, 772, 784, 790, 806, 827, 840, 855, 860, 871, 989, 999, 1043, 1055, 1070

Interface 116, 215, 410, 434, 440, 452, 458, 473, 483, 489, 494, 520, 531, 537, 543, 567, 573, 591, 632, 670, 692, 724, 741, 761, 767, 779, 840, 867, 883, 903, 947, 999, 1015, 1070, 1072, 1076

Iron
- organic 274

Kinetics
- of growth 1, 13, 32, 37, 47, 62, 68, 73, 102, 111, 116, 136, 147, 175, 221, 226, 281, 331, 337, 348, 355, 376, 390, 410, 513, 537, 583, 621, 644, 649, 653, 710, 761, 840, 850, 860,

883, 903, 909, 915, 952, 969, 982, 989, 999, 1015, 1021, 1038, 1040, 1041, 1047, 1049, 1053, 1055, 1062, 1065
– of interface control 68
– of nucleation 68, 116

Lasers 192, 403, 561, 716, 724, 731, 741, 751, 757, 761, 767, 779, 784, 790, 796, 802, 806, 827, 850, 871, 978
Lattice mismatch 96, 166, 175, 188, 215, 445, 489, 496, 518, 520, 549, 555, 573, 637, 674, 679, 692, 731, 751, 790, 796, 806, 822, 871, 932, 978, 999, 1051, 1057
Light emitting diode 822, 832

Magnesium
– organic 254, 883, 893
Manganese
– organic 632
Melt growth technique
– by Bridgman–Stockbarger method
– – of gallium indium arsenide 396
– by zone melting
– – of gallium indium arsenide 396
Mercury
– cadmium telluride 297, 598, 605, 610, 621, 626, 632
Morphology of growth 102, 116, 147, 161, 203, 215, 231, 237, 337, 360, 376, 390, 410, 416, 428, 468, 494, 509, 531, 583, 610, 626, 659, 670, 692, 1047

Nitrogen
– organic 281
Nucleation 1068, 1072
Numbers
– Grashof 1
– Reynolds 410

Optoelectronics 156, 806, 840, 855, 871, 878, 1065

Perfection of crystals 434, 458, 468, 483, 494, 502, 626, 632, 664, 674, 779, 822, 1065
Phase diagrams 396, 416, 683, 699
Phenomenological theory 489
Phosphorus
– organic 12, 281, 351, 365, 1021
Precursor 13, 32, 73, 116, 254, 281, 290, 297, 309, 319, 325, 348, 355, 360, 365, 376, 386, 390, 644
Purification of materials 281, 1068

Quantum wells/size effects 83, 96, 116, 147, 161, 166, 243, 403, 422, 452, 518, 520, 531, 537, 543, 549, 555, 561, 567, 573, 578, 583, 591, 716, 724, 731, 741, 751, 757, 761, 772, 779, 784, 796, 802, 806, 845, 860, 871, 932, 947, 960, 999, 1060, 1076

Safety instrumentation 281, 290, 314
Segregation 396
Selenium
– organic 390, 644, 653, 670, 674, 679, 836, 1072
Silicon 1015
Solar cells 410
Step 237, 243, 263
Strain 458, 468, 479, 489, 496, 513, 518, 543, 555, 567, 578, 583, 637, 731, 741, 796, 822, 827, 836, 915, 921, 926
Strontium
– organic 683, 692, 705, 712
– titanate 712
Sulphur
– organic 644, 674, 679
Superconductivity 683, 692, 699, 705, 710
– characterization 683, 692, 699, 705, 710
– crystal chemistry 683, 692, 699, 705, 710
– high T_c 683, 692, 699, 705, 710
– phase relationships 683, 699
– thin films 683, 692, 699, 705, 710
Superlattices 102, 231, 452, 468, 479, 518, 822, 827, 956, 1051
Surface processes 37, 47, 56, 537, 1068, 1072
Surface structure 37, 47, 68, 237, 263, 351, 473, 494, 496, 692, 878, 903, 932, 1047, 1068

Tellurium
– organic 319, 325, 605, 621, 626, 836, 1043
Thallium
– barium calcium cuprate 683
– organic 683
Thermodynamics 56, 116, 416, 871
Thin film growth
– by atomic layer epitaxy
– – of aluminum gallium arsenide 47, 83, 89
– – of gallium arsenide 47, 62, 73, 83, 102
– – of gallium indium phosphide 96
– – of gallium phosphide 102
– by chemical beam epitaxy
– – of aluminum gallium arsenide 1040
– – of gallium arsenide 969, 1051
– – of gallium indium arsenide 969, 1038, 1055, 1057
– – of gallium indium arsenide phosphide 978
– – of indium phosphide 1055
– – of III–V compounds 960, 999
– by gas source molecular beam epitaxy
– – of aluminum gallium arsenide 1030
– – of gallium arsenide 1070
– – of germanium 1015
– – of indium phosphide 1070
– – of silicon 1015
– – of III–V compounds 960, 999
– by metalorganic molecular beam epitaxy
– – of aluminum gallium arsenide 982, 1045, 1068
– – of gallium arsenide 982, 1036, 1041, 1043, 1045, 1049, 1053, 1076
– – of gallium indium arsenide 989, 1060, 1062, 1065, 1074
– – of gallium indium phosphide 1076
– – of indium aluminum arsenide antimonide 1009
– – of indium phosphide 989, 1043
– – of III–V compounds 960, 1009, 1021
– – of zinc selenide 1072
– by molecular beam epitaxy
– – of aluminum gallium arsenide 520

– by vapor phase epitaxy
– – through metalorganic chemical vapor deposition
– – – of aluminum arsenide 231, 479
– – – of aluminum gallium arsenide 47, 83, 116, 161, 175, 226, 237, 243, 268, 350, 370, 428, 434, 452, 483, 591, 716, 757, 767, 779, 832, 845, 883, 893, 898, 903, 909, 915, 921, 947, 956
– – – of aluminum gallium indium phosphide 192, 403, 578, 724
– – – of aluminum nitride 376
– – – of cadmium telluride 664
– – – of ferroelectric oxides 712
– – – of gallium antimonide 181, 422, 952
– – – of gallium arsenide 1, 12, 26, 32, 37, 47, 56, 62, 68, 73, 83, 111, 116, 129, 136, 161, 434, 440, 452, 468, 473, 479, 483, 489, 496, 583, 591, 644, 716, 757, 767, 772, 822, 855, 878, 883, 893, 898, 903, 909, 915, 921, 926, 942, 947, 956, 1047
– – – of gallium arsenide phosphide 479, 513
– – – of gallium indium antimonide 952
– – – of gallium nitride 376, 509
– – – of gallium phosphide 573
– – of high T_c superconductors 683, 692, 699, 705, 710
– – – of indium aluminum arsenide 555, 932
– – – of indium arsenide 175, 188, 226, 231, 243, 248, 259, 263, 279, 281, 290, 331, 337, 342, 348, 370, 422, 428, 952
– – – of indium arsenide antimonide 83
– – – of indium gallium aluminum arsenide 784, 806
– – – of indium gallium arsenide 116, 141, 147, 151, 175, 365, 370, 445, 520, 531, 537, 543, 549, 555, 567, 573, 583, 731, 741, 751, 784, 790, 796, 802, 840, 850, 855, 860, 871, 915, 921, 942, 989
– – – of indium gallium arsenide phosphide 209, 215, 221, 549, 561, 751, 761, 796, 802, 806, 827, 850, 860, 867, 871
– – – of indium gallium phosphide 151, 192, 351, 724, 942
– – – of indium phosphide 26, 156, 175, 188, 203, 254, 274, 355, 360, 365, 381, 494, 573, 731, 772, 784, 790, 806, 827, 840, 855, 871, 989
– – – of mercury cadmium telluride 297, 598, 605, 610, 621, 626, 632
– – – of III–V compounds 166, 281, 309, 458, 518
– – – of III–V compounds, bismuth containing 416
– – – of II–VI compounds 202, 297, 637
– – – of zinc cadmium sulphide 674
– – – of zinc cadmium sulphoselenide 674
– – – of zinc chalcogenides 637, 644
– – – of zinc selenide 386, 390, 653, 659, 670, 679
– – – of zinc silicide diarsenide 410
– – – of zinc sulphide 649
– – – of zinc sulphoselenide 679
Three–five (III–V) compounds 102, 166, 188, 209, 281, 309, 458, 518, 772, 960
Tin
– organic 836, 1043
Titanium
– organic 712
Transistor 840, 883, 893, 898, 903, 909, 915, 921, 926, 942, 952
Twinning 664
Two–six (II–VI) compounds 202, 297, 598, 637

Uniformity of growth 102, 116, 136, 166, 175, 181, 192, 221, 281, 370, 445, 761, 784, 855, 893, 898, 942, 999

Yttrium
– barium cuprate 683, 699, 710
– organic 683, 699, 710

Zinc
– cadmium sulphide 674
– cadmium sulphoselenide 674
– chalcogenides 644
– organic 141, 156, 254, 274, 386, 390, 410, 649, 653, 659, 670, 674, 679, 731, 751, 761, 767, 772, 796, 802, 822, 827, 832, 860, 871, 878, 898, 909, 1043, 1072
– selenide 386, 390, 653, 659, 670, 679, 1072
– silicon diarsenide 410
– sulphide 649
– sulphoselenide 679
Zirconium
– organic 381